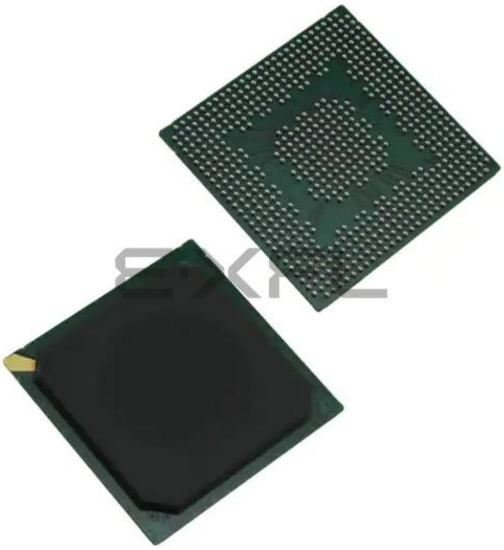
NXP USA Inc. - MPC8343ZQADD Datasheet



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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8343zqadd

  - Can operate as a stand-alone USB host controller
    - USB root hub with one downstream-facing port
    - Enhanced host controller interface (EHCI) compatible
    - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
  - External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects for eight external slaves
  - Up to eight-beat burst transfers
  - 32-, 16-, and 8-bit port sizes controlled by an on-chip memory controller
  - Three protocol engines on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user-programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
  - Functional and programming compatibility with the MPC8260 interrupt controller
  - Support for 8 external and 35 internal discrete interrupt sources
  - Support for 1 external (optional) and 7 internal machine checkstop interrupt sources
  - Programmable highest priority request
  - Four groups of interrupts with programmable priority
  - External and internal interrupts directed to host processor
  - Redirects interrupts to external $\overline{\text{INTA}}$ pin in core disable mode.
  - Unique vector number for each interrupt source
- Dual industry-standard I^2C interfaces
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
  - System initialization data optionally loaded from I^2C-1 EPROM by boot sequencer embedded hardware
- DMA controller
  - Four independent virtual channels
  - Concurrent execution across multiple channels with programmable bandwidth control
  - Handshaking (external control) signals for all channels: $\overline{\text{DMA\_DREQ}}$[0:3], $\overline{\text{DMA\_DACK}}$[0:3], $\overline{\text{DMA\_DDONE}}$[0:3]
  - All channels accessible to local core and remote PCI masters

supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{PORESET}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

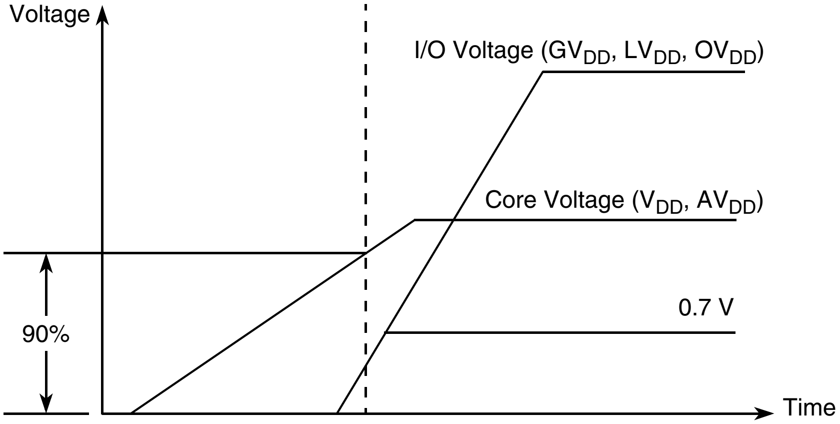

Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

3 Power Characteristics

The estimated typical power dissipation for the MPC8343EA device is shown in Table 4.

Table 4. MPC8343EA Power Dissipation[1]

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T_J = 65	Typical[2,3]	Maximum[4]	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W

[1] The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.

[2] Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.

[3] Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.

[4] Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 13 provides the DDR2 capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 13. DDR2 SDRAM Capacitance for $GV_{DD}(typ) = 1.8$ V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8\ V \pm 0.090$ V, f = 1 MHz, $T_A = 25°C$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when $GV_{DD}(typ) = 2.5$ V.

Table 14. DDR SDRAM DC Electrical Characteristics for $GV_{DD}(typ) = 2.5$ V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.18$	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current ($V_{OUT} = 1.95$ V)	I_{OH}	–15.2	—	mA	—
Output low current ($V_{OUT} = 0.35$ V)	I_{OL}	15.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0\ V \leq V_{OUT} \leq GV_{DD}$.

Table 15 provides the DDR capacitance when $GV_{DD}(typ) = 2.5$ V.

Table 15. DDR SDRAM Capacitance for $GV_{DD}(typ) = 2.5$ V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 2.5\ V \pm 0.125$ V, f = 1 MHz, $T_A = 25°C$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

8.1.1 TSEC DC Electrical Characteristics

MII, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. The RGMII and RTBI signals in Table 24 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}[2]	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = -4.0$ mA	LV_{DD} = Min	2.40	$LV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 4.0$ mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	$LV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	40	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–600	—	μA

Notes:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 24. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0$ mA	LV_{DD} = Min	2.00	$LV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0$ mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	$LV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–15	—	μA

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 MII, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for MII, RGMII, and RTBI are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

Table 25 provides the MII transmit AC timing specifications.

Table 25. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 9 shows the MII transmit AC timing diagram.

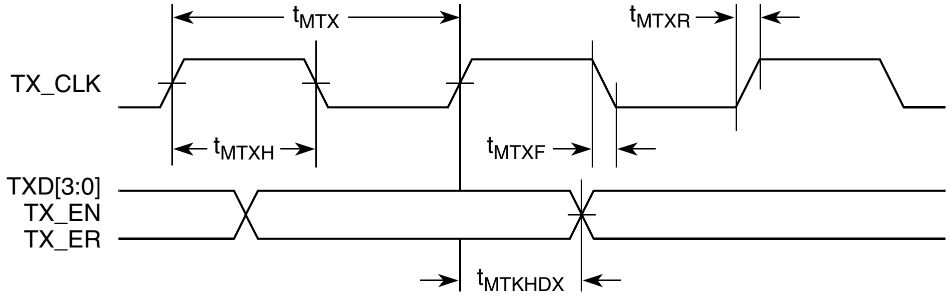

Figure 9. MII Transmit AC Timing Diagram

8.2.2 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–0.5	—	0.5	ns
Data to clock input skew (at receiver)[2]	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration[3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T[4, 5]	t_{RGTH}/t_{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX[3, 5]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (80%–20%)	t_{RGTF}	—	—	0.75	ns

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).
2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
5. Duty cycle reference is $LV_{DD}/2$.

Figure 12 shows the RBMII and RTBI AC timing and multiplexing diagrams.

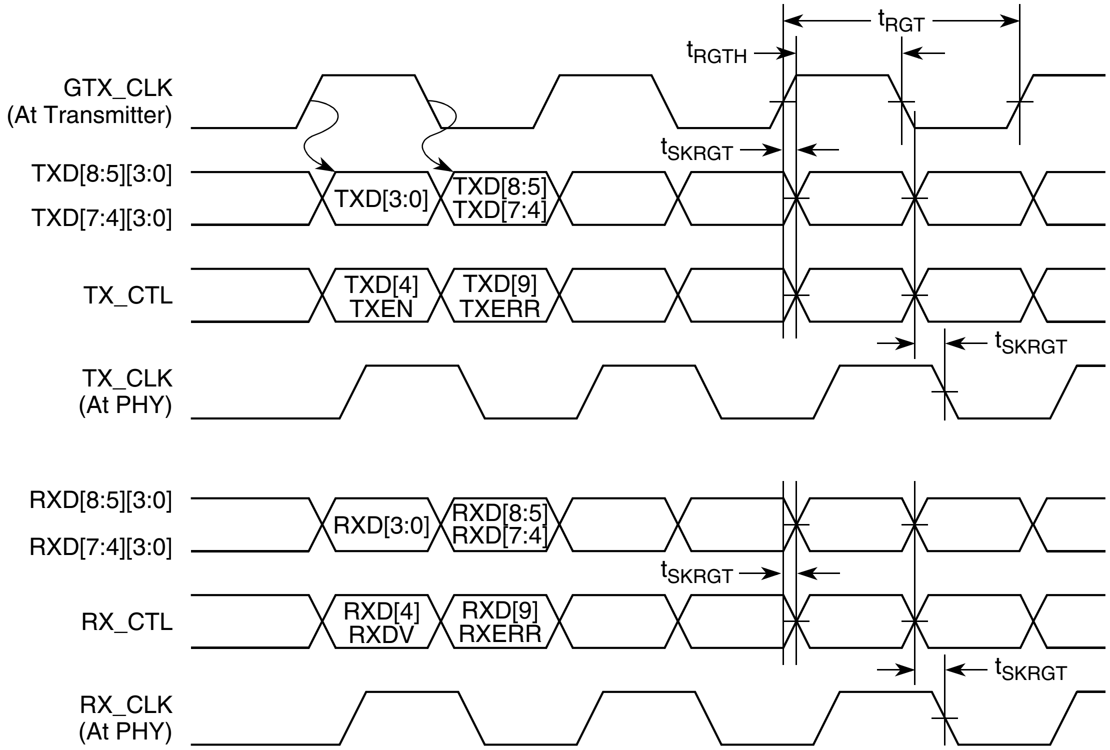

Figure 12. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, “Three-Speed Ethernet Controller (TSEC)—MII/RGMII/RTBI Electrical Characteristics.”

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 28 and Table 29.

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (2.5 V)	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	—	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8343EA.

9.1 USB DC Electrical Characteristics

Table 31 provides the DC electrical characteristics for the USB interface.

Table 31. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, $I_{OH} = -100$ μA	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100$ μA	V_{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 32 describes the general timing parameters of the USB interface of the MPC8343EA.

Table 32. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	t_{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	2–5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

10.2 Local Bus AC Electrical Specification

Table 34 and Table 35 describe the general timing parameters of the local bus interface of the MPC8343EA.

Table 34. Local Bus General Timing Parameters—DLL On

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.5	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	2.2	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT Input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	1	—	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	8

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the rising edge of LSYNC_IN.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin equals the load on the LAD output pins.
8. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

Table 35. Local Bus General Timing Parameters—DLL Bypass[9]

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to output valid	t_{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.the
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin equals to the load on the LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 16 provides the AC test load for the local bus.

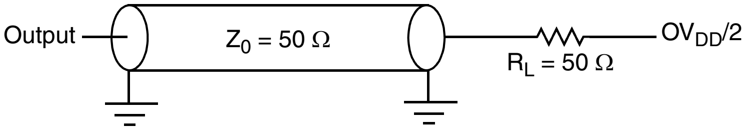

Figure 16. Local Bus C Test Load

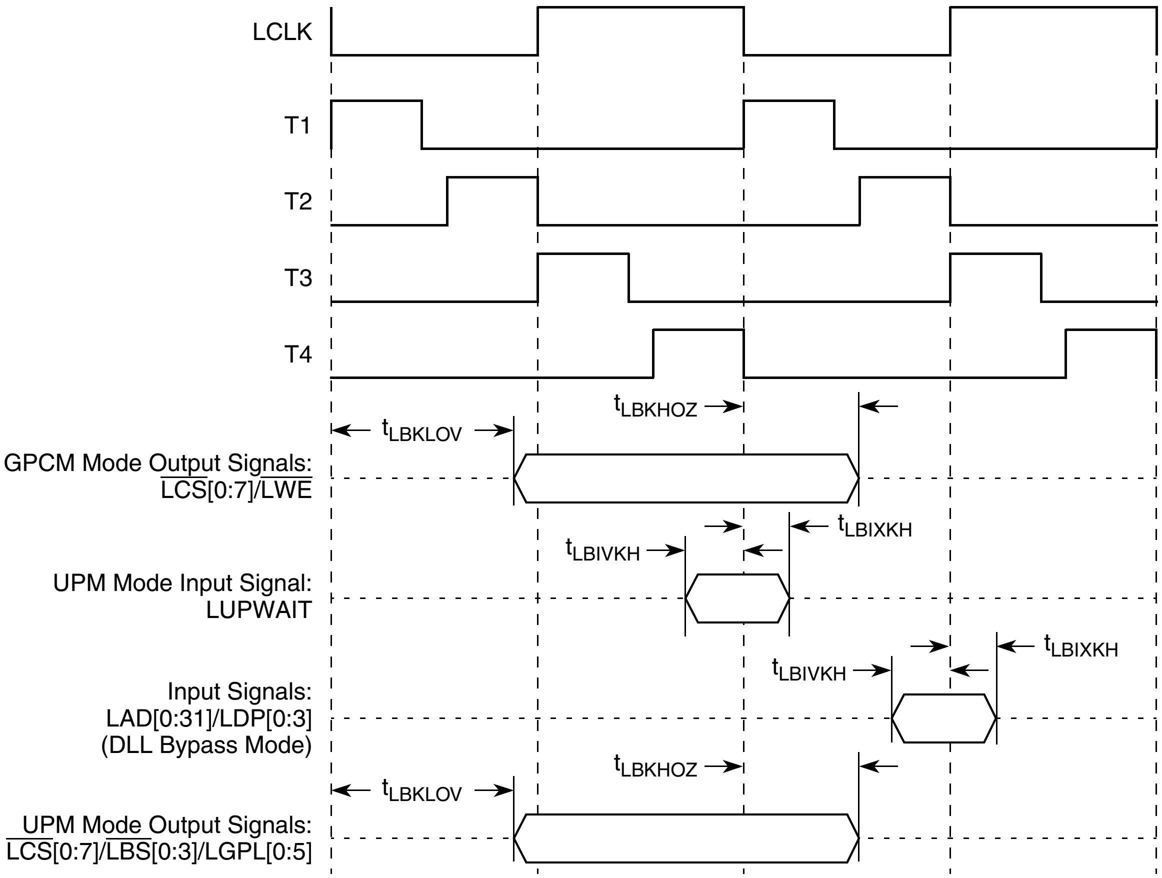

Figure 21. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

12 I^2C

This section describes the DC and AC electrical characteristics for the I^2C interface of the MPC8343EA.

12.1 I^2C DC Electrical Characteristics

Table 38 provides the DC electrical characteristics for the I^2C interface of the MPC8343EA.

Table 38. I^2C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual,* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I^2C AC Electrical Specifications

Table 39 provides the AC timing parameters for the I^2C interface of the MPC8343EA. Note that all values refer to V_{IH}(min) and V_{IL}(max) levels (see Table 38).

Table 39. I^2C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time:CBUS compatible masters I^2C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Table 39. I^2C AC Electrical Specifications (continued)

Parameter	Symbol[1]	Min	Max	Unit
Fall time of both SDA and SCL signals[5]	t_{I2CF}	—	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^2C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^2C timing (I2) for the time that the data with respect to the start condition (S) goes invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^2C timing (I2) for the time that the data with respect to the stop condition (P) reaches the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} must be met only if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.
5.)The device does not follow the “I2C-BUS Specifications” version 2.1 regarding the tI2CF AC parameter.

Figure 28 provides the AC test load for the I^2C.

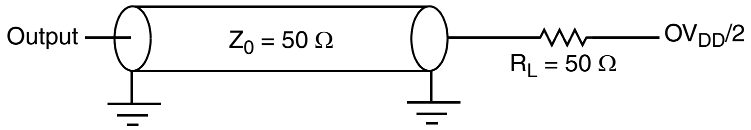

Figure 28. I^2C AC Test Load

Figure 29 shows the AC timing diagram for the I^2C bus.

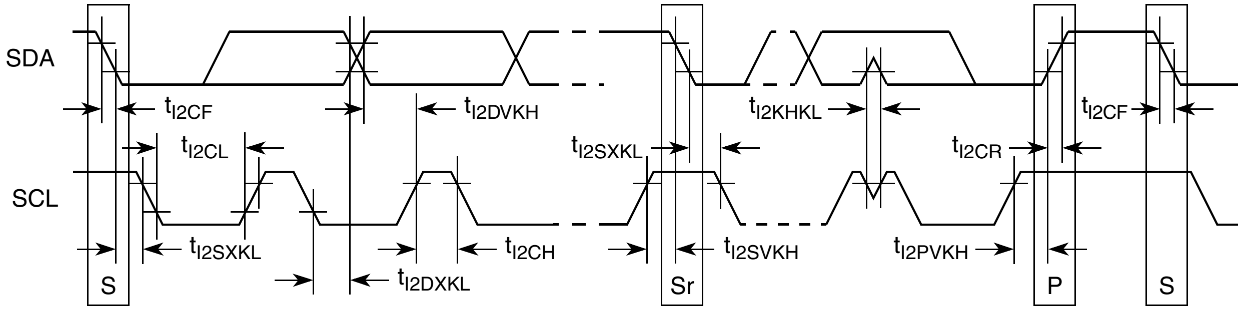

Figure 29. I^2C Bus AC Timing Diagram

Figure 31 shows the PCI input AC timing diagram.

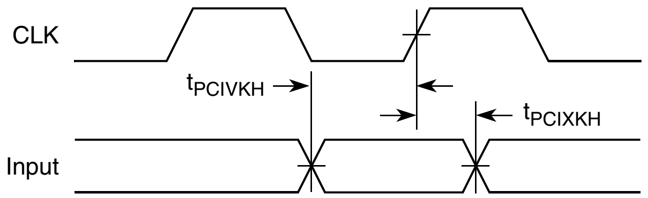

Figure 31. PCI Input AC Timing Diagram

Figure 32 shows the PCI output AC timing diagram.

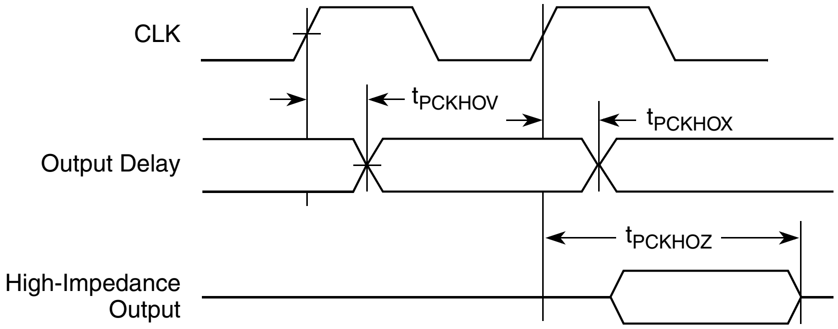

Figure 32. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the MPC8343EA timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 43. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MECC[0:4]/MSRCID[0:4]	AG13, AE14, AH12, AH10, AE15	I/O	GV$_{DD}$	—
MECC[5]/MDVAL	AH14	I/O	GV$_{DD}$	—
MECC[6:7]	AE13, AH11	I/O	GV$_{DD}$	—
MDM[0:3]	AG28, AG24, AF20, AG17	O	GV$_{DD}$	—
MDM[8]	AG12	O	GV$_{DD}$	—
MDQS[0:3]	AE27, AE26, AE20, AH18	I/O	GV$_{DD}$	—
MDQS[8]	AH13	I/O	GV$_{DD}$	—
MBA[0:1]	AF10, AF11	O	GV$_{DD}$	—
MA[0:14]	AF13, AF15, AG16, AD16, AF17, AH20, AH19, AH21, AD18, AG21, AD13, AF21, AF22, AE1, AA5	O	GV$_{DD}$	—
$\overline{\text{MWE}}$	AD10	O	GV$_{DD}$	—
$\overline{\text{MRAS}}$	AF7	O	GV$_{DD}$	—
$\overline{\text{MCAS}}$	AG6	O	GV$_{DD}$	—
$\overline{\text{MCS}}$[0:3]	AE7, AH7, AH4, AF2	O	GV$_{DD}$	—
MCKE[0:1]	AG23, AH23	O	GV$_{DD}$	3
MCK[0:3]	AH15, AE24, AE2, AF14	O	GV$_{DD}$	—
$\overline{\text{MCK}}$[0:3]	AG15, AD23, AE3, AG14	O	GV$_{DD}$	—
MODT[0:3]	AG5, AD4, AH6, AF4	O	GV$_{DD}$	—
MBA[2]	AD22	O	GV$_{DD}$	—
MDIC0	AG11	I/O	—	9
MDIC1	AF12	I/O	—	9
Local Bus Controller Interface				
LAD[0:31]	T4, T5, T1, R2, R3, T2, R1, R4, P1, P2, P3, P4, N1, N4, N2, N3, M1, M2, M3, N5, M4, L1, L2, L3, K1, M5, K2, K3, J1, J2, L5, J3	I/O	OV$_{DD}$	—
LDP[0]/$\overline{\text{CKSTOP\_OUT}}$	H1	I/O	OV$_{DD}$	—
LDP[1]/$\overline{\text{CKSTOP\_IN}}$	K5	I/O	OV$_{DD}$	—
LDP[2]/$\overline{\text{LCS}}$[4]	H2	I/O	OV$_{DD}$	—
LDP[3]/$\overline{\text{LCS}}$[5]	G1	I/O	OV$_{DD}$	—
LA[27:31]	J4, H3, G2, F1, G3	O	OV$_{DD}$	—
$\overline{\text{LCS}}$[0:3]	J5, H4, F2, E1	O	OV$_{DD}$	—
$\overline{\text{LWE}}$[0:3]/LSDDQM[0:3]/$\overline{\text{LBS}}$[0:3]	F3, G4, D1, E2	O	OV$_{DD}$	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
USB				
DR_D0_ENABLEN	C28	I/O	OV$_{DD}$	—
DR_D1_SER_TXD	F25	I/O	OV$_{DD}$	—
DR_D2_VMO_SE0	B28	I/O	OV$_{DD}$	—
DR_D3_SPEED	C27	I/O	OV$_{DD}$	—
DR_D4_DP	D26	I/O	OV$_{DD}$	—
DR_D5_DM	E25	I/O	OV$_{DD}$	—
DR_D6_SER_RCV	C26	I/O	OV$_{DD}$	—
DR_D7_DRVVBUS	D25	I/O	OV$_{DD}$	—
DR_SESS_VLD_NXT	B26	I	OV$_{DD}$	—
DR_XCVR_SEL_DPPULLUP	E24	I/O	OV$_{DD}$	—
DR_STP_SUSPEND	A27	O	OV$_{DD}$	—
DR_RX_ERROR_PWRFAULT	C25	I	OV$_{DD}$	—
DR_TX_VALID_PCTL0	A26	O	OV$_{DD}$	—
DR_TX_VALIDH_PCTL1	B25	O	OV$_{DD}$	—
DR_CLK	A25	I	OV$_{DD}$	—
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	E8	O	OV$_{DD}$	2
$\overline{\text{IRQ0}}$/MCP_IN/GPIO2[12]	J28	I/O	OV$_{DD}$	—
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV$_{DD}$	—
$\overline{\text{IRQ}}$[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV$_{DD}$	—
$\overline{\text{IRQ}}$[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV$_{DD}$	—
Ethernet Management Interface				
EC_MDC	Y24	O	LV$_{DD1}$	—
EC_MDIO	Y25	I/O	LV$_{DD1}$	11
Gigabit Reference Clock				
EC_GTX_CLK125	Y26	I	LV$_{DD1}$	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	M26	I/O	OV$_{DD}$	—
TSEC1_CRS/GPIO2[21]	U25	I/O	LV$_{DD1}$	—
TSEC1_GTX_CLK	V24	O	LV$_{DD1}$	3
TSEC1_RX_CLK	U26	I	LV$_{DD1}$	—

Table 55. CSB Frequency Options for Host Mode (continued)

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
High	0010	2 : 1				133
High	0011	3 : 1			100	200
High	0100	4 : 1			133	266
High	0101	5 : 1			166	333
High	0110	6 : 1			200	
High	0111	7 : 1			233	
High	1000	8 : 1				

[1] CFG_CLKIN_DIV selects the ratio between CLKIN and PCI_SYNC_OUT.

[2] CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

Table 56. CSB Frequency Options for Agent Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266

Table 57. e300 Core PLL Configuration (continued)

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider[1]
0–1	2–5	6		
00	**0010**	0	2:1	2
01	**0010**	0	2:1	4
10	**0010**	0	2:1	8
11	**0010**	0	2:1	8
00	**0010**	1	2.5:1	2
01	**0010**	1	2.5:1	4
10	**0010**	1	2.5:1	8
11	**0010**	1	2.5:1	8
00	**0011**	0	3:1	2
01	**0011**	0	3:1	4
10	**0011**	0	3:1	8
11	**0011**	0	3:1	8

[1] Core VCO frequency = core frequency × VCO divider. The VCO divider must be set properly so that the core VCO frequency is in the range of 800–1800 MHz.

19.3 Suggested PLL Configurations

Table 58 shows suggested PLL configurations for 33 and 66 MHz input clocks, when CFG_CLKIN_DIV is low at reset.

Table 58. Suggested PLL Configurations

Ref No.[1]	RCWL		266 MHz Device			333 MHz Device			400 MHz Device		
	SPMF	CORE PLL	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)
33 MHz CLKIN/PCI_CLK Options											
343	**0011**	**1000011**	33	100	150	33	100	150	33	100	150
324	**0011**	**0100100**	33	100	200	33	100	200	33	100	200
423	**0100**	**0100011**	33	133	200	33	133	200	33	133	200
622	**0110**	**0100010**	33	200	200	33	200	200	33	200	200
523	**0101**	**0100011**	33	166	250	33	166	250	33	166	250
424	**0100**	**0100100**	33	133	266	33	133	266	33	133	266
822	**1000**	**0100010**	33	266	266	33	266	266	33	266	266

Table 60. Heat Sink and Thermal Resistance of MPC8343EA (PBGA) (continued)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	7.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	6.6
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	6.9

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

Heat sink vendors include the following list:

Aavid Thermalloy 603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Alpha Novatech 408-567-8082
473 Sapena Ct. #12
Santa Clara, CA 95054
Internet: www.alphanovatech.com

International Electronic Research Corporation (IERC) 818-842-7277
413 North Moss St.
Burbank, CA 91502
Internet: www.ctscorp.com

Millennium Electronics (MEI) 408-436-8770
Loroco Sites
671 East Brokaw Road
San Jose, CA 95112
Internet: www.mei-thermal.com

Tyco Electronics 800-522-2800
Chip Coolers™
P.O. Box 3668
Harrisburg, PA 17105-3668
Internet: www.chipcoolers.com

Wakefield Engineering 603-635-5102
33 Bridge St.
Pelham, NH 03076
Internet: www.wakefield.com

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